

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

SASAKI et al.

Examiner:

Unknown

10/809,033

Group Art Unit:

Unknown

Filed:

March 25, 2004

Docket:

10873.1440US01

Title:

METHOD OF MANUFACTURING GROUP III NITRIDE SINGLE CRYSTAL, DEVICE USED FOR THE METHOD AND GROUP III NITRIDE SINGLE CRYSTAL OBTAINED BY

THE METHOD

**CERTIFICATE UNDER 37 CFR 1.8:** 

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail, with sufficient postage, in an envelope addressed to: Mail Stop Amendments, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450 on September 23, 2004.

Name: Jennife

Mail Stop Amendments Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

PATENT TRADEMARK OFFICE

Sir:

We are transmitting herewith the attached:

☐ Transmittal Sheet in duplicate containing Certificate of Mailing

☐ Information Disclosure Statement, Form 1449, 3 References

Return postcard

Please consider this a PETITION FOR EXTENSION OF TIME for a sufficient number of months to enter these papers or any future reply, if appropriate. Please charge any additional fees or credit overpayment to Deposit Account No. 13-2725. A duplicate of this sheet is enclosed.

MERCHANT & GOULD P.C. P.O. Box 2903, Minneapolis, MN 55402-0903 612.332.5300

By: iglas P. Mueller Name: Do

Reg. No. 30,300

DPM/jh

PATENT



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Name: Jennifer Holden

## **INFORMATION DISCLOSURE STATEMENT (37 C.F.R. § 1.97(b))**

Mail Stop Amendments

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Dear Sir:

With regard to the above-identified application, the items of information listed on the enclosed Form 1449 are brought to the attention of the Examiner.

This statement should be considered because it is submitted before the mailing date of a first Office Action on-the-merits. Accordingly, no fee is due for consideration of the items listed on the enclosed Form 1449.

In accordance with 37 C.F.R. §1.98(a)(2), a copy of each document or other information listed on the enclosed Form 1449 is provided.

No representation is made that a reference is "prior art" within the meaning of 35 U.S.C. §§ 102 and 103 and Applicants reserve the right, pursuant to 37 C.F.R. § 1.131 or otherwise, to establish that the reference(s) are not "prior art." Moreover, Applicants do not represent that a reference has been thoroughly reviewed or that any relevance of any portion of a reference is intended.

Consideration of the items listed is respectfully requested. Pursuant to the provisions of M.P.E.P. 609, it is requested that the Examiner return a copy of the attached Form 1449, marked as being considered and initialed by the Examiner, to the undersigned with the next official communication.

Please charge any additional fees or credit any overpayment to Deposit Account No. 13-2725.

Respectfully submitted,

MERCHANT & GOULD P.C. P.O. Box 2903 Minneapolis, MN 55402-0903 (612) 332-5300

Dated: September 23, 2004

Bv:

Douglas P. Mueller Reg. No. 30,300

DPM/jh

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PATENT TRADEMARK OFFICE

FORM 1449P ENFORMATION DISCLOSURE STATEMENT	Docket Number: 10873.1440US01	Application Number: 10/809,033		
SEP 2 7 2004 D IN AN APPLICATION	Applicant: SASAKI et al.			
(Use several sheets if necessary)	Filing Date: March 25, 2004	Group Art Unit: Unknown		

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Imade et a	al., "Growth of l	Bulk GaN Single Crystals b	y High-Pressure		od", Proceedi	ngs of the
Imade et a	al. "Growth of T , Jpn. J. Appl. P	Thick GaN Films with High hys., Vol. 43 (2004), pp. L4	Growth Rate Us 86-L488	sing Sublimation M	ethod under l	High
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EXAMINER	DATE CONSIDERED	

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form for next communication to the Applicant.